

Inchange Semiconductor

Product Specification

Silicon NPN Darlington Power Transistors

2SD2439

DESCRIPTION

- With TO-3PML package
- Complement to type 2SB1588

APPLICATIONS

- Audio ,series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

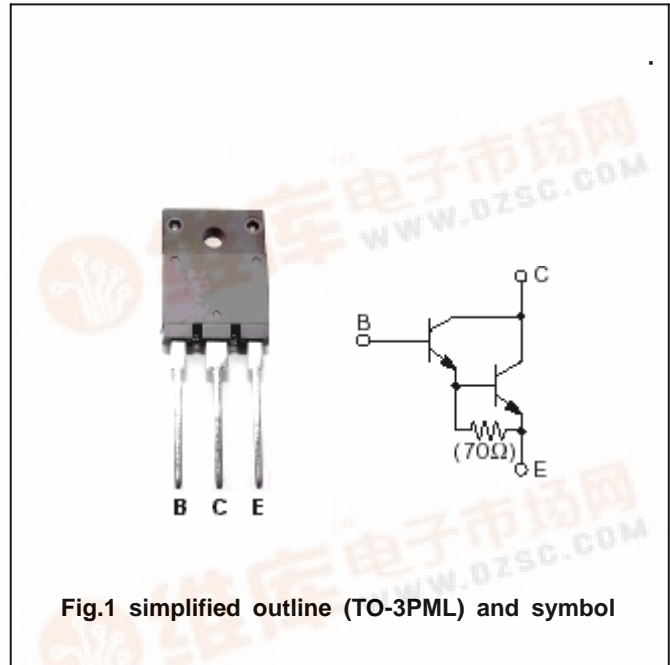


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0	150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =7 A; I _B =7m A			2.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =7 A; I _B =7m A			3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =160V ; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =7A ; V _{CE} =4V	5000			
f _T	Transition frequency	I _C =2A ; V _{CE} =12V		55		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		95		pF

Switching times

t _{on}	Turn-on time	I _C =7A; R _L =10 I _{B1} =-I _{B2} =7mA V _{CC} =70V		0.5		μ s
t _s	Storage time			10.0		μ s
t _f	Fall time			1.1		μ s

◆ h_{FE} classifications

O	P	Y
5000-12000	6500-20000	15000-30000

